

BAV19W, BAV20W, BAV21W

Silicon Epitaxial Planar Diodes

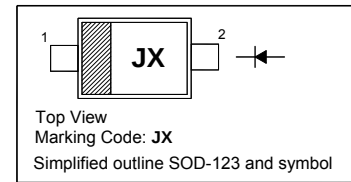
High Voltage Switching Diode

Features

- Fast switching speed
- Surface mount package ideally suited for automatic insertion

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

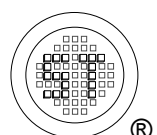


Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	V
		200	
		250	
Reverse Voltage	V_R	100	V
		150	
		200	
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Forward Continuous Current	I_{FM}	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	2.5	A
		0.5	
Power Dissipation	P_d	250	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

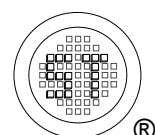
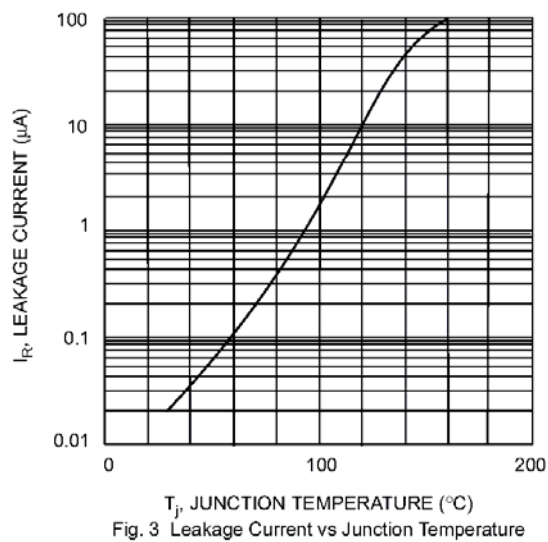
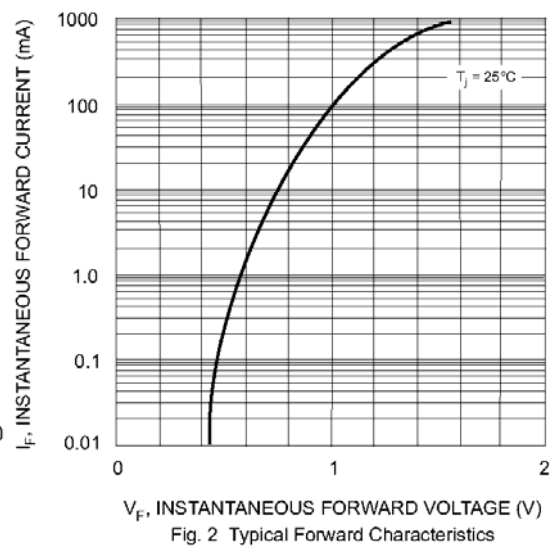
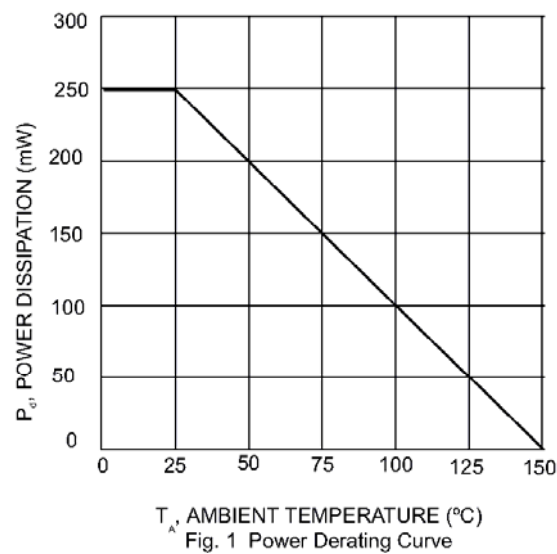
Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	-	1	V
		-	1.25	
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	120	-	V
		200	-	
		250	-	
Reverse Current at $V_R = 100\text{ V}$ at $V_R = 150\text{ V}$ at $V_R = 200\text{ V}$	I_R	-	100	nA
		-	100	
		-	100	
Total Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_T	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}$, $I_{rr} = 0.1I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	50	ns



Dated : 15/06/2009

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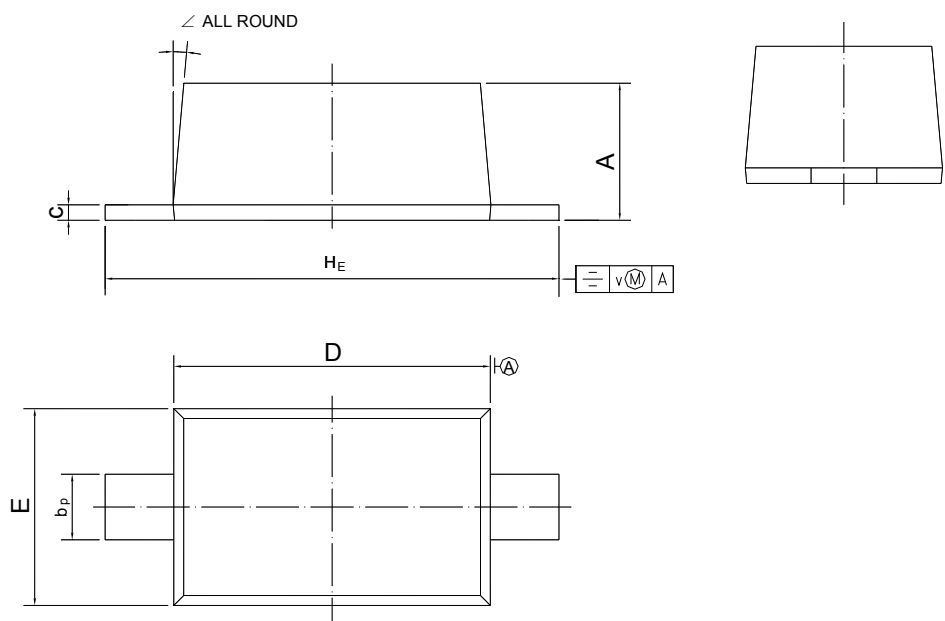


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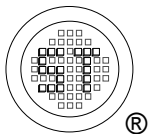
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°



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